

MA4X174

Silicon planar type

For small power rectification and surge absorption

■ Features

- Two isolated elements contained in one package, allowing high-density mounting
- High voltage (V_R : 200 V) rectification is possible

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	V_R	200	V
Repetitive peak reverse voltage	V_{RRM}	250	V
Non-repetitive peak forward surge current	V_{RSM}	300	V
Output current*1	I_O	100	mA
Repetitive peak forward current*1	I_{FRM}	225	mA
Non-repetitive peak forward surge current*1,2	I_{FSM}	500	mA
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +125	$^\circ\text{C}$

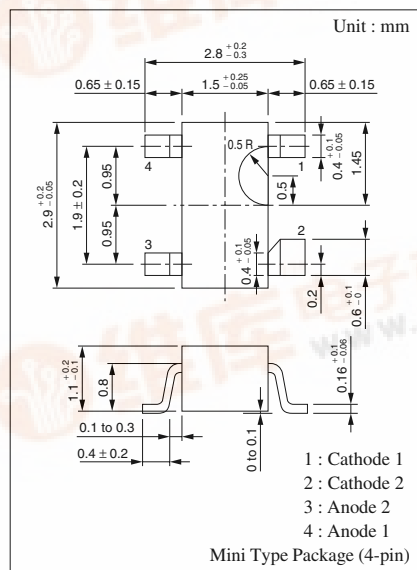
Note) *1 : Value in single diode used

*2: $t = 1 \text{ s}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current (DC)	I_R	$V_R = 200 \text{ V}$			1.0	μA
Forward voltage (DC)	V_F	$I_F = 100 \text{ mA}$			1.3	V

Note) 1. Rated input/output frequency: 3 MHz



Marking Symbol: M2Q

Internal Connection

